# SK200DHL066



SEMITOP<sup>®</sup>4

Half controlled bridge rectifier + IGBT braking chopper SK200DHL066

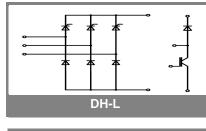
Target Data

### Features

- · One screw mounting hole
- · Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT brake chopper technology
- CAL technology free-wheeling diode chopper

## Typical Applications\*

- V<sub>CE,sat</sub>, V<sub>F</sub> = chip level value
- $I_{CM} = 2xI_{Cnom}$ ,  $t_p \le 1ms$
- $I_{FM} = 2xI_{Fnom}$ ,  $t_p \le 1ms$   $I_C = I_{Cnom}$ ,  $I_F = I_{Fnom}$

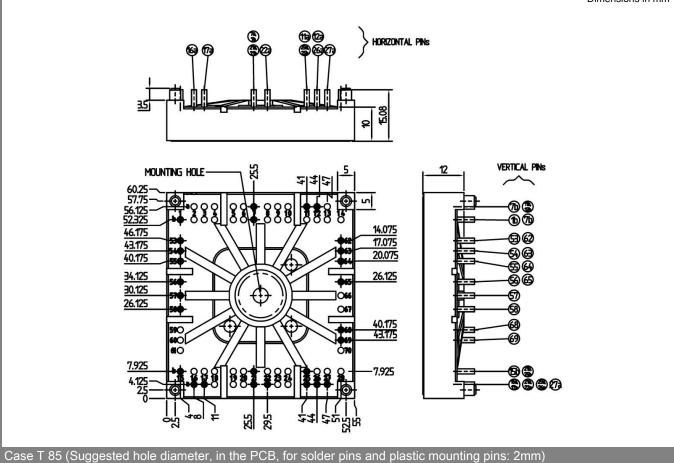


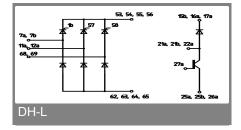
#### I<sub>D</sub> = 210 A (maximum value for continuous operation) V<sub>RSM</sub> V<sub>RRM</sub>, V<sub>DRM</sub> (T<sub>s</sub> = 70 °C) V v T<sub>s</sub>=25°C, unless othwerwise specified Absolute Maximum Ratings Symbol |Conditions Values Units **Bridge - Rectifier** T<sub>s</sub> = 70 °C; inductive load 210 А $I_D$ 1250 t<sub>n</sub> = 10 ms; half sine wave, ;T<sub>imax</sub> А I<sub>ESM</sub>/I<sub>TSM</sub> t<sub>n</sub> = 10 ms; half sine wave, ;T<sub>imax</sub> i²t 7810 A²s **IGBT - Chopper** 600 / 20 V<sub>CES</sub>/V<sub>GES</sub> V T<sub>o</sub> = 25 (70) °C 174 (131) А Ι<sub>C</sub> $t_p = 1 \text{ ms}; T_s = °C$ 400 A I<sub>CM</sub> Freewheeling - CAL Diode V<sub>RRM</sub> 600 V T<sub>s</sub> = 25 (70) °C 100 (80) А $I_{F}$ $t_p = 1 \text{ ms}; T_s = °C$ 200 А $I_{FM}$ T<sub>vj</sub> °C Diode & IGBT (Thyristor) -40 ... +150 (-40 ... +130) T<sub>stg</sub> -40 ... +125 (-40 ... +130) °C T<sub>solder</sub> terminals, 10 s 260 °C 2500 / 3000 V a.c. 50 Hz, RMS 1 min. / 1 s V<sub>isol</sub> Characteristics Symbol |Conditions Units min. typ. max. **Diode - Rectifier** T; = 125 °C 0,8/4 V/mΩ V<sub>TO</sub> / r<sub>t</sub> R<sub>th(j-s)</sub> K/W per diode 0,52 **Thyristor - Rectifier** T<sub>i</sub> = 130 °C 1,1/4,5 V / mO V<sub>F(TO)</sub> / r<sub>t</sub> $\mathsf{R}_{\mathsf{th}(\mathsf{j-s})}$ K/W per Thyristor 0,44 T<sub>i</sub> = 115 °C; d.c. 6 mΑ I<sub>GD</sub> T<sub>i</sub> = 25 °C 1,98 / 100 V / mA V<sub>GT</sub> / I<sub>GT</sub> T<sub>i</sub> = 25 °C 220 / 550 mΑ $I_{H}/I_{L}$ (dv/dt)<sub>cr</sub> T<sub>i</sub> = 130 °C 1000 V/µs T<sub>i</sub> = 130 °C (di/dt)<sub>cr</sub> 100 A/µs **IGBT - Chopper** I<sub>C</sub> = 200 A, T<sub>j</sub> = 125 °C; V<sub>GE</sub> = 15 V V V<sub>CE(sat)</sub> 1,7 2,15 per IGBT R<sub>th(j-s)</sub> 0,45 K/W valid for all values: t<sub>d(on)</sub> / t<sub>r</sub> ns $V_{CC} = 300 \text{ V}; V_{GE} = 15 \text{ V};$ $I_{C} = 200 \text{ A}; T_{j} = 125 ^{\circ}\text{C};$ $t_{d(off)}$ / $t_{f}$ ns $E_{on}+E_{off}$ T<sub>i</sub> = 125 °C; R<sub>G</sub> = 4 Ω; 13,8 mJ inductive load CAL - Diode - Freewheeling 0,85/3,5 T<sub>i</sub> = 150 °C V / mΩ $V_{T(TO)} / r_t$ $\mathsf{R}_{\mathsf{th}(\underline{\mathsf{j}}-\underline{\mathsf{s}})}$ K/W per diode 0,8 valid for all values: А RRM I<sub>F</sub> = 200 A; V<sub>R</sub> = - 600 V; dI<sub>F</sub>/dt = - A/μs μC $Q_{rr}$ $\mathsf{E}_{\mathsf{off}}$ V<sub>GE</sub> = V; T<sub>i</sub> = 125 °C mJ **Temperature Sensor** T = °C: Ω R<sub>TS</sub> Mechanical data mounting Torque Nm $M_{S}$ 2,5 2,75

### 12-05-2008 DIL

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Dimensions in mm





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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